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# The spin-double refraction in two-dimensional electron gas

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**Abstract**

We briefly review the phenomenon of the spin-double refraction that originates at an interface separating a two-dimensional electron gas with Rashba spin-orbit coupling from a one without. We demonstrate how this phenomenon in semiconductor heterostructures can produce and control a spin-polarized current without ferromagnetic leads.

*Key words:* Rashba effect, spin-FET
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Spintronics is a multidisciplinary field whose central subject is the active control and manipulation of spin degrees of freedom in solid-state systems [1,2]. The attempts to realize the spin Field-Effect Transistor (spin-FET) proposed by Datta and Das [3], based on Rashba Spin-Orbit (SO) coupling [4], have been unsuccessful because of the difficulty of inject spin-polarized carriers from a ferromagnetic metal into a semiconductor [5]. One of the way to solve the problem of the conductivity mismatch at the ferromagnet-semiconductor interface is to use dilute magnetic semiconductor as input source [6].

We have proposed [7] an alternative way to overcome the problem of the conductivity mismatch. In this work we consider the phenomenon of the spin-double refraction. A similar effect has been successively presented by Khodas *et al.* [8]. This is observed in two-Dimensional Electron Gas (2DEG) when electrons are injected with an angle out of the normal on an interface separating a region without Rashba SO coupling (NR zone) from a region with

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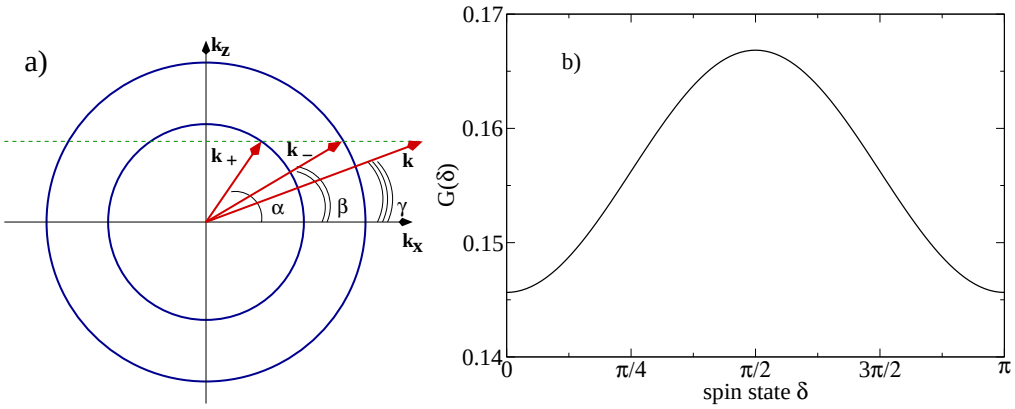



Fig. 1. Panel a): the vectors $\vec{k}_+$, $\vec{k}_-$ and $\vec{k}$ in $k$-space and the angles $\alpha$, $\beta$ and $\gamma$ that they form with $x$ direction normal to the interface. The two circles are the Fermi contour at a fixed energy. Panel b): the conductance for polarized electrons $\mathcal{G}$ as a function of the spin polarization $\delta$ of the incoming electrons. The value $\delta = 0$ corresponds to spin up and $\delta = \pi/2$ to spin down.

it (R zone). The behavior of electron spin in such scattering is analogous to the polarization of the light in a biaxial crystal: the incident ray splits, within the crystal, in two rays (ordinary and extraordinary) whose polarizations are orthogonal.

The Hamiltonian describing the hybrid system is

$$\mathcal{H}_{\text{NR-R}} = \vec{p}\frac{1}{2m(x)}\vec{p} + \frac{k_{\text{SO}}(x)m(x)}{\hbar^2}\left(\sigma_z p_x - \sigma_x p_z\right) - i\sigma_z\frac{1}{2}\frac{\partial k_{\text{SO}}(x)}{\partial x} + U\delta(x). \quad (1)$$

The second term is the Rashba SO coupling. The presence of the interface is introduced by the mass and the strength of SO coupling that are piecewise constant

$$\frac{1}{m}(x) = \frac{\vartheta(-x)}{m_{\text{NR}}} + \frac{\vartheta(x)}{m_{\text{R}}} \quad \text{and} \quad k_{\text{SO}}(x) = k_{\text{SO}}\,\vartheta(x), \quad (2)$$

where $\vartheta(x)$ is the step function. The third term in (1) is needed to get an hermitian operator $\mathcal{H}_{\text{NR-R}}$ and the fourth term regulates the transparency of the interface. Let us consider an electron injected from the NR zone on the interface with momentum $k$ and angle $\gamma$. The electron wave function in the R zone is given by the superposition of the split eigenstates of the R zone, whose directions are fixed by the conservation of the momentum parallel to the interface

$$k_+ \sin\alpha = k_- \sin\beta = k \sin k \quad (3)$$

where $k_\pm = \sqrt{\mu k^2 + k_{\text{SO}}^2} \mp k_{\text{SO}}$ is the momentum relative to the two eigenstates (see Fig. 1 Panel a) and $\mu = m_{\text{N}}/m_{\text{NR}}$. The two eigenstates of the R zone are characterized by two limit angles

$$\gamma_0 = \arcsin\frac{k_+}{k} \quad \text{and} \quad \gamma_1 = \arcsin\frac{k_-}{k} > \gamma_0 \quad (4)$$

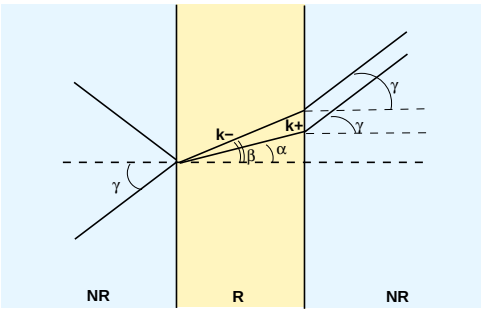



Fig. 2. Schematic illustration of the proposed devices. The two-dimensional electron gas is divided in three region. In central region a Rashba spin-orbit coupling is present.

over which they become non propagative waves. The analysis of the transmission probability of the hybrid system shows that in the case of normal incidence the interface is not able to distinguish spin up and spin down electrons. Instead, the oblique scattering, due to the spin-double refraction, gives rise to an output spin up probability different from the spin down probability [7]. This effect of polarization survives also when all the injection angles are taken into account ($-\gamma_1 < \gamma < \gamma_1$). This is equivalent to consider the transmission through a wide point contact devices. In the Fig. 1 Panel b) is shown the behavior of the conductance $\mathcal{G}$ of this system as function of the spin state $\delta$. It is evident that the conductance of the single interface when the incoming spin is up ($\delta = 0, \pi$) is different from the conductance when the incoming spin state is down ($\delta = \pi/2$). This effect is a direct consequence of the spin-double refraction at the interface that change the spin state when the electron comes into the R zone.

This phenomenon can be used to realize an spin-FET without ferromagnetic contacts [9]. The system is realized in a 2DEG where a region in which the Rashba SO coupling is present (see Fig.2). The source and the drain could be realized using $n^+$-semiconductors. The novel feature of our setup is the transmission double step shown in Fig. 3 Panel a), that is accompanied by the appearance of a spin polarization. This is due to the spin-double refraction, when $\gamma$ goes over $\gamma_0$ only one mode of the R zone can reach the second interface and the transmission coefficients tend to halve themself. The dependence of the limit angle $\gamma_0$ on the SO strength $k_{\rm SO}$ suggests the possibility to build up a spin-FET operating on spin unpolarized electrons injected in the R region. The electrons emerge in the NR drain region partially polarized with a polarization controlled by a gate electrode via the SO interaction. There is a SO strength $\overline{k}_{\rm SO}$ at which $\gamma = \gamma_0$. The Fig. 3 Panel b) shows that the transmission coefficient exhibits irregular Fabry-Perot oscillations below $\overline{k}_{\rm SO}$, whereas for $k_{\rm SO} > \overline{k}_{\rm SO}$ the oscillations become regular with maxima equal to 1/2. The threshold $\overline{k}_{\rm SO}$ is determined by the parameters of the Hamiltonian of the hybrid system [9]. When $k_{\rm SO} > \overline{k}_{\rm SO}$ the polarization of electrons in the NR drain $P_{\rm out}$ is equal to $T$. We get a source of a spin polarized current controlling

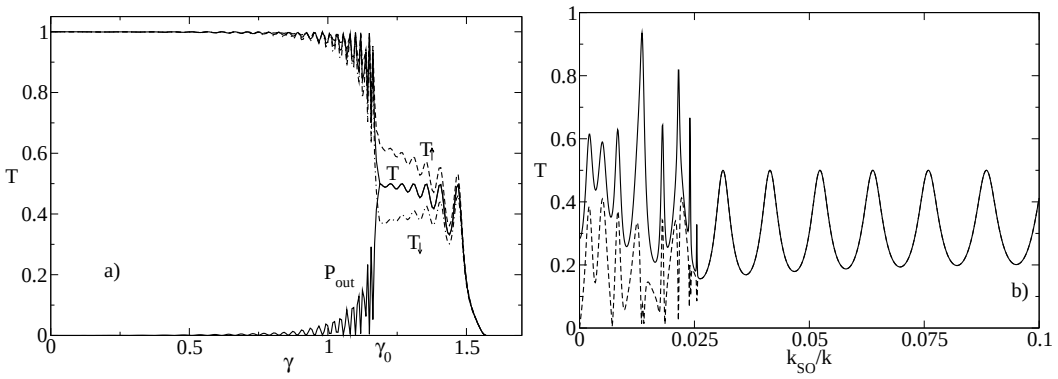



Fig. 3. Panel a): The transmission coefficients $T_\downarrow(\gamma)$, $T(\gamma)$, $T_\uparrow(\gamma)$ as functions of the incidence angle $\gamma$ (in radians). Panel b): The transmission coefficient for unpolarized electrons when $\gamma = 1.25$. The threshold $\overline{k}_{SO}$ is $0.025k$. The dotted curve gives the output spin polarization, the length of the Rashba zone is $L = 283$ nm.

$k_{\rm SO}$ with a gate. We stress that a modulation of the output current can be obtained with a spin-unpolarized input current, whereas in the original Datta and Das [3] proposal the current oscillation stems out from the difference of phase accumulated along a path in the Rashba region by the two spin propagating modes. In our system the current modulation and the spin polarization appear when *only one mode* propagates through the Rashba barrier.

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